

**ECE-656: Fall 2011**

**Lecture 26:**

**Phonon Scattering: III**

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# transition rate for phonon scattering

$$S(\vec{p}, \vec{p}') = \frac{2\pi}{\hbar} |H_{p,p'}|^2 \delta(E' - E \mp \hbar\omega) \quad H_{p',p} = \frac{1}{\Omega} \int_{-\infty}^{+\infty} e^{-i\vec{p}'\cdot\vec{r}/\hbar} U_S(\vec{r}) e^{i\vec{p}\cdot\vec{r}/\hbar} d\vec{r}$$

$$U_S(\vec{r}) = K_\beta u_\beta \quad u_\beta(\vec{r}) = A_\beta e^{\pm i\vec{\beta}\cdot\vec{r}} \quad |H_{p',p}|^2 = |K_\beta|^2 |A_\beta|^2 \delta_{\vec{p}', \vec{p} \pm \hbar\vec{\beta}}$$

$$|A_\beta|^2 \rightarrow \frac{\hbar}{2\rho\Omega\omega} \left( N_\omega + \frac{1}{2} \mp \frac{1}{2} \right)$$

$$S(\vec{p}, \vec{p}') = \frac{\pi}{\Omega\rho\omega} |K_\beta|^2 \left( N_\omega + \frac{1}{2} \mp \frac{1}{2} \right) \delta_{\vec{p}', \vec{p} \pm \hbar\vec{\beta}} \delta(E' - E \mp \hbar\omega)$$

# transition rate for phonon scattering

$$S(\vec{p}, \vec{p}') = \frac{\pi}{\Omega \rho \omega} |K_\beta|^2 \left( N_\omega + \frac{1}{2} \mp \frac{1}{2} \right) \delta_{\vec{p}', \vec{p} \pm \hbar \vec{\beta}} \delta(E' - E \mp \hbar \omega)$$

ADP  $|K_\beta|^2 = \beta^2 D_A^2$

PZ  $|K_\beta|^2 = (q e_{PZ} / \kappa_S \epsilon_0)^2$

ODP  $|K_\beta|^2 = D_0^2$

POP  $|K_\beta|^2 = \frac{\rho q^2 \omega_0^2}{\beta^2 \kappa_0 \epsilon_0} \left( \frac{\kappa_0}{\kappa_\infty} - 1 \right)$

# energy-momentum conservation

$$S(\vec{p}, \vec{p}') = \frac{2\pi}{\hbar} |K_\beta|^2 |A_\beta|^2 \delta_{\vec{p}', \vec{p} \pm \hbar \vec{\beta}} \delta(E' - E \mp \hbar \omega)$$

$$\vec{p}' = \vec{p} \pm \hbar \vec{\beta} \quad E' = E \pm \hbar \omega_\beta$$

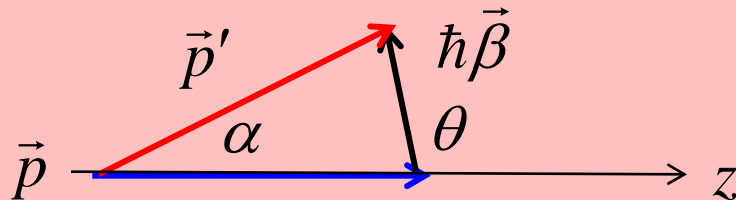
$$\delta_{\vec{p}', \vec{p} \pm \hbar \vec{\beta}} \delta(E' - E \mp \hbar \omega_\beta) \rightarrow \frac{1}{\hbar v \beta} \delta\left(\pm \cos \theta + \frac{\hbar \beta}{2p} \mp \frac{\omega_\beta}{v \beta}\right)$$

# final answer: transition rate

$$S(\vec{p}, \vec{p}') = \frac{2\pi}{\hbar} |K_\beta|^2 \frac{\hbar}{2\rho\Omega\omega} \frac{1}{\hbar\nu\beta} \left( N_\omega + \frac{1}{2} \mp \frac{1}{2} \right) \delta \left( \pm \cos\theta + \frac{\hbar\beta}{2p} \mp \frac{\omega}{\nu\beta} \right)$$

$$S(\vec{p}, \vec{p}') = \frac{1}{\Omega} C_\beta \left( N_\omega + \frac{1}{2} \mp \frac{1}{2} \right) \delta \left( \pm \cos\theta + \frac{\hbar\beta}{2p} \mp \frac{\omega}{\nu\beta} \right)$$

$$C_\beta = \frac{\pi}{\hbar\rho\nu\omega\beta} |K_\beta|^2 \quad N_\omega = \frac{1}{e^{\hbar\omega/k_B T} - 1}$$



# general expression for the phonon scattering rate

$$\frac{1}{\tau} = \sum_{\vec{p}', \uparrow} S(\vec{p}, \vec{p}') = \sum_{\vec{\beta}, \uparrow} S(\vec{p}, \vec{p}') \quad \vec{p}' = \vec{p} \pm \hbar \vec{\beta}$$

Integration of the delta function simply restricts  $\beta$  to those values that satisfy energy and momentum conservation.

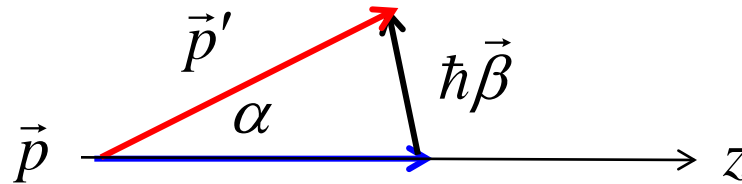
$$\beta_{\min} < \beta < \beta_{\max}$$

$$\frac{1}{\tau} = \frac{1}{4\pi^2} \int_{\beta_{\min}}^{\beta_{\max}} C_{\beta} \left( N_{\omega} + \frac{1}{2} \mp \frac{1}{2} \right) \beta^2 d\beta$$

$$C_{\beta} = \frac{\pi}{\hbar \rho v \omega \beta} |K_{\beta}|^2 \quad N_{\omega} = \frac{1}{e^{\hbar\omega/k_B T} - 1}$$

# momentum relaxation rate

$$\frac{1}{\tau_m} = \sum_{\vec{p}', \uparrow} S(\vec{p}, \vec{p}') \frac{(\Delta p_z)}{p_z} = \sum_{\vec{p}', \uparrow} S(\vec{p}, \vec{p}') \left( 1 - \frac{p'}{p} \cos \alpha \right)$$



$$\frac{1}{\tau_m} = \frac{1}{4\pi^2} \int_{\beta_{\min}}^{\beta_{\max}} C_{\beta} \left( N_{\omega} + \frac{1}{2} \mp \frac{1}{2} \right) \left( \frac{\hbar\beta}{2p} \mp \frac{\omega_{\beta}}{v\beta} \right) \frac{\hbar\beta^3}{p} d\beta$$

# outline

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- 1) Review
- 2) Example**
- 3) POP and IV scattering
- 4) Scattering in common semiconductors
- 5) Electron-electron scattering
- 6) Summary

(Reference: Chapter 2, Lundstrom, FCT)



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# acoustic phonon scattering

$$\frac{1}{\tau} = \frac{1}{4\pi^2} \int_{\beta_{\min}}^{\beta_{\max}} C_{\beta} \left( N_{\omega} + \frac{1}{2} \mp \frac{1}{2} \right) \beta^2 d\beta$$

$$C_{\beta} = \frac{\pi m^* D_A^2}{\hbar \rho v_s p} \quad (\text{Lundstrom, FCT, p. 79})$$

$$N_{\omega} = \frac{1}{e^{\hbar\omega_s/k_B T_L} - 1} \quad \hbar\omega_s \ll k_B T_L \rightarrow N_{\omega_s} \approx \frac{k_B T_L}{\hbar\omega_s} \approx N_{\omega_s} + 1$$

“equipartition”

$$\frac{1}{\tau_{abs}} = \frac{1}{\tau_{ems}} = \frac{1}{4\pi^2} \int_{\beta_{\min}}^{\beta_{\max}} \frac{\pi m^* D_A^2 k_B T_L}{\hbar \rho v_s p \hbar \omega_s} \beta^2 d\beta$$

# acoustic phonon scattering (ii)

$$\frac{1}{\tau_{abs}} = \frac{1}{\tau_{ems}} = \frac{m^* D_A^2 k_B T_L}{4\pi \hbar^2 \rho v_s p} \int_{\beta_{min}}^{\beta_{max}} \frac{\beta}{\omega_s} \beta d\beta \quad v_s = \sqrt{c_l / \rho}$$

$$\frac{1}{\tau_{abs}} = \frac{1}{\tau_{ems}} = \frac{m^* D_A^2 k_B T_L}{4\pi \hbar^2 c_l p} \int_{\beta_{min}}^{\beta_{max}} \beta d\beta = \frac{m^* D_A^2 k_B T_L}{4\pi \hbar^2 c_l p} \left( \frac{\beta_{max}^2}{2} - \frac{\beta_{min}^2}{2} \right)$$

elastic scattering:  $\hbar\beta_{max} = 2p$

$$\hbar\beta_{min} = 0$$

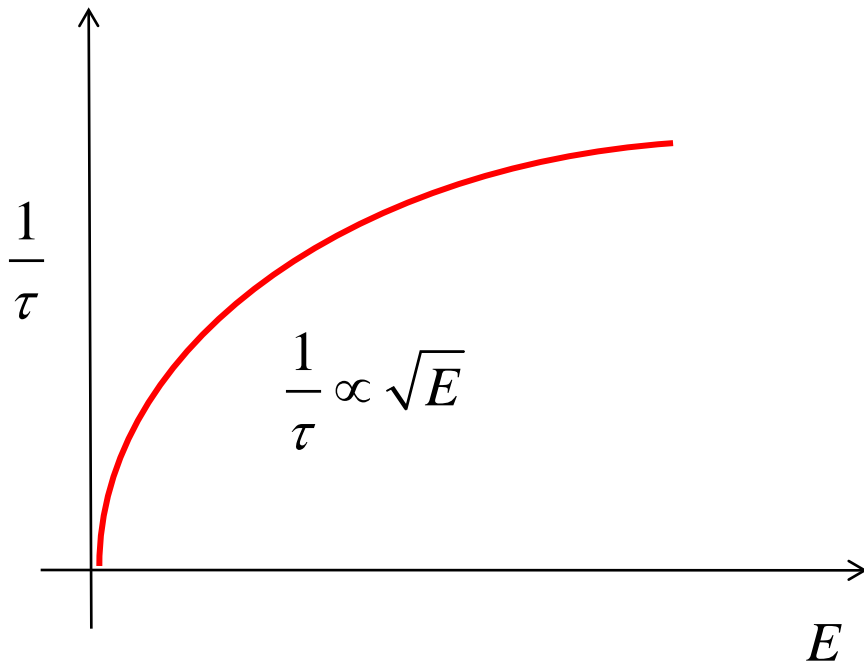
$$\frac{1}{\tau_{abs}} = \frac{1}{\tau_{ems}} \quad \frac{1}{\tau} = \frac{1}{\tau_{abs}} + \frac{1}{\tau_{ems}}$$

# acoustic phonon scattering (iii)

$$\frac{1}{\tau} = \frac{1}{\tau_{abs}} + \frac{1}{\tau_{ems}} = \frac{2\pi}{\hbar} \left( \frac{D_A^2 k_B T}{c_l} \right) \frac{D_{3D}(E)}{2}$$

$$\frac{1}{\tau} = \frac{1}{\tau_m}$$

(isotropic)



# optical deformation potential scattering

$$\frac{1}{\tau} = \frac{1}{4\pi^2} \int_{\beta_{\min}}^{\beta_{\max}} C_{\beta} \left( N_{\omega} + \frac{1}{2} \mp \frac{1}{2} \right) \beta^2 d\beta$$

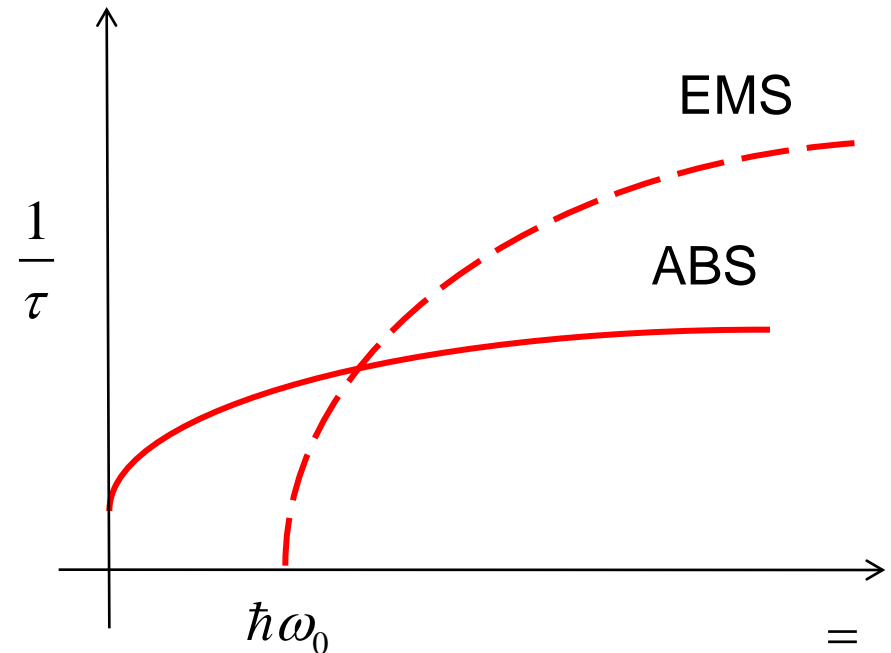
$$C_{\beta} = \frac{\pi m^* D_o^2}{\hbar \rho \omega_0 \beta p}$$

(Lundstrom, FCT, p. 79)

$$N_0 = \frac{1}{e^{\hbar\omega_0/k_B T_L} - 1}$$

$$\frac{1}{\tau} = \frac{1}{\tau_m} = \frac{2\pi}{\hbar} \left( \frac{\hbar D_o^2}{2\rho\omega_0} \right) \left( N_0 + \frac{1}{2} \mp \frac{1}{2} \right) \frac{D_{3D}(E \pm \hbar\omega_0)}{2}$$

$$\frac{1}{\tau_{abs}} \neq \frac{1}{\tau_{ems}}$$



# isotropic vs. anisotropic scattering

$$\frac{1}{\tau} = \frac{1}{4\pi^2} \int_{\beta_{\min}}^{\beta_{\max}} C_{\beta} \left( N_{\omega} + \frac{1}{2} \mp \frac{1}{2} \right) \beta^2 d\beta \quad C_{\beta} = \frac{\pi m^* D_0^2}{\hbar \rho \omega_0 \beta p}$$

How do we determine whether scattering is isotropic?

Go back to the matrix element:

$$|H_{p',p}|^2 = \frac{1}{\Omega} |K_{\beta}|^2 \frac{\hbar}{2\rho \omega_0} \left( N_0 + \frac{1}{2} \mp \frac{1}{2} \right) \delta_{\vec{p}', \vec{p} \pm \hbar \vec{\beta}}$$

$$|K_{\beta}|^2 = D_0^2 \quad N_0 = \frac{1}{e^{\hbar\omega_0/k_B T} - 1}$$

No dependence on  $\beta \rightarrow$  isotropic scattering.

# short cut for isotropic scattering

$$S(\vec{p}, \vec{p}') = \frac{2\pi}{\hbar} |H_{p,p'}|^2 \delta(E' - E \mp \hbar\omega)$$

$$U_s(\vec{r}) = K_\beta u_\beta \quad u_\beta(\vec{r}) = A_\beta e^{\pm i\vec{\beta}\cdot\vec{r}} \quad |H_{p',p}|^2 = |K_\beta|^2 |A_\beta|^2 \delta_{\vec{p}', \vec{p} \pm \hbar\vec{\beta}}$$

$$S(\vec{p}, \vec{p}') = \frac{2\pi}{\hbar} |K_\beta|^2 |A_\beta|^2 \delta_{\vec{p}', \vec{p} \pm \hbar\vec{\beta}} \delta(E' - E \mp \hbar\omega)$$

For isotropic scattering:

$$S(\vec{p}, \vec{p}') = \frac{2\pi}{\hbar} |K_\beta|^2 |A_\beta|^2 \delta(E' - E \mp \hbar\omega)$$

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# POP scattering

$$S(\vec{p}, \vec{p}') \approx \frac{2\pi}{\hbar} |H_{p,p'}|^2 \delta(E' - E \pm \hbar\omega_0) \quad (\text{inelastic at RT and below})$$

$$|H_{p',p}|^2 = \frac{1}{\Omega} |K_\beta|^2 \frac{\hbar}{2\rho\omega_0} \left( N_0 + \frac{1}{2} \mp \frac{1}{2} \right) \delta_{\vec{p}', \vec{p} \pm \hbar\vec{\beta}} \quad N_0 = \frac{1}{e^{\hbar\omega_0/k_B T} - 1} < N_0 + 1$$

$$|K_\beta|^2 = \frac{\rho q^2 \omega_0^2}{\beta^2 \kappa_0 \epsilon_0} \left( \frac{\kappa_0}{\kappa_\infty} - 1 \right) \quad (\text{favors small angle scattering})$$

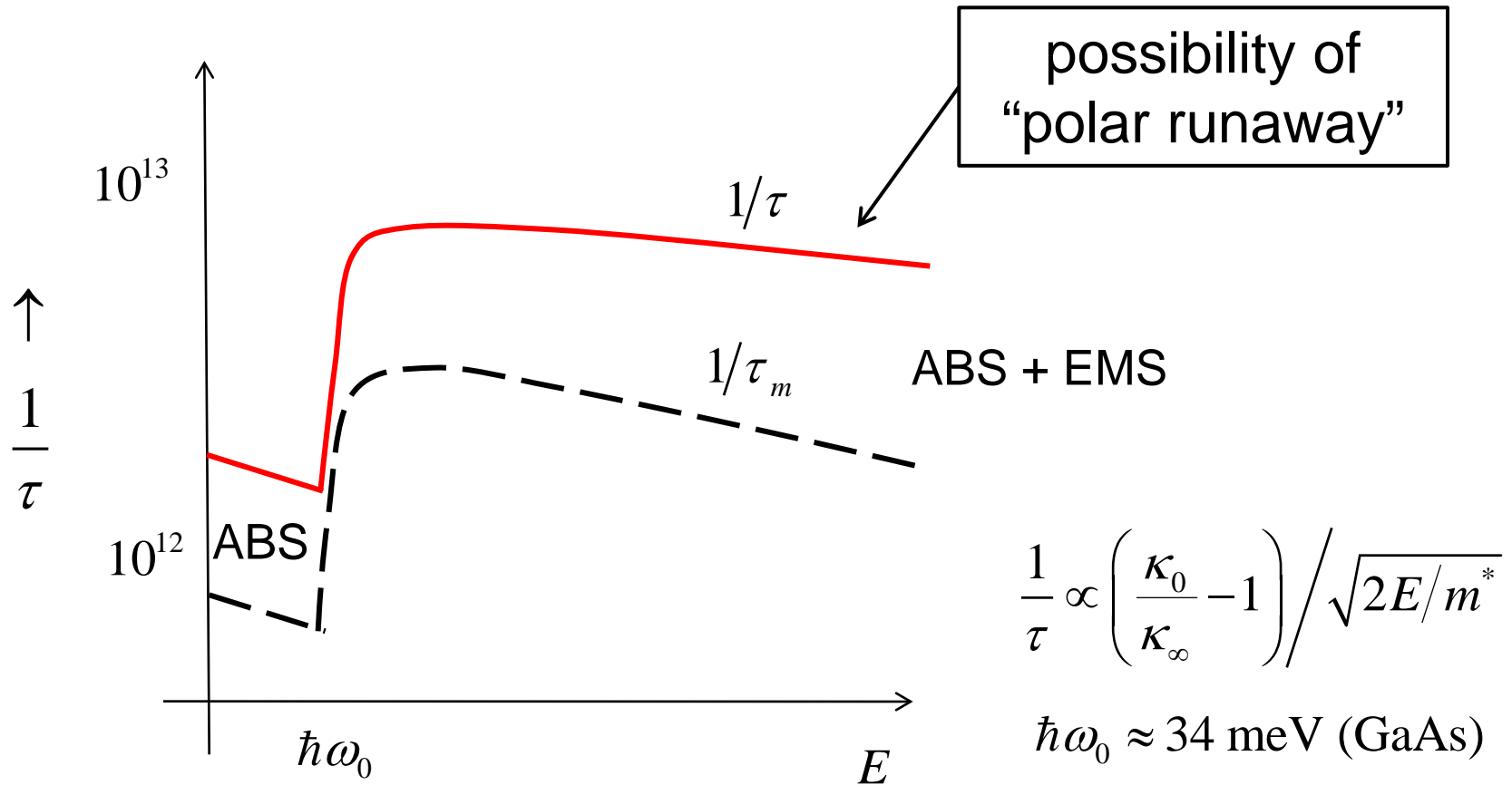
$$\frac{1}{\tau} = \frac{1}{\tau_{abs}} + \frac{1}{\tau_{ems}} = \frac{q^2 \omega_0^2 \left( \frac{\kappa_0}{\kappa_\infty} - 1 \right)}{2\pi \kappa_0 \epsilon_0 \hbar \sqrt{2E/m^*}} \left[ N_0 \sinh^{-1} \left( \frac{E}{\hbar\omega_0} \right) + (N_0 + 1) \sinh^{-1} \left( \frac{E}{\hbar\omega_0} - 1 \right) \right]$$

$$\frac{1}{\tau} > \frac{1}{\tau_m} > \frac{1}{\tau_E}$$

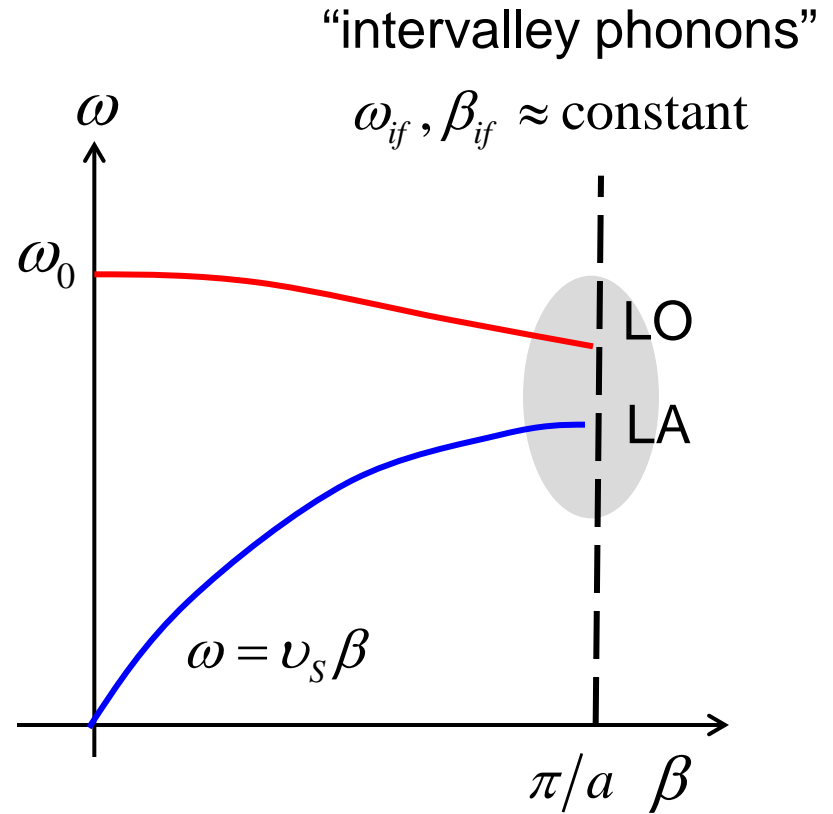
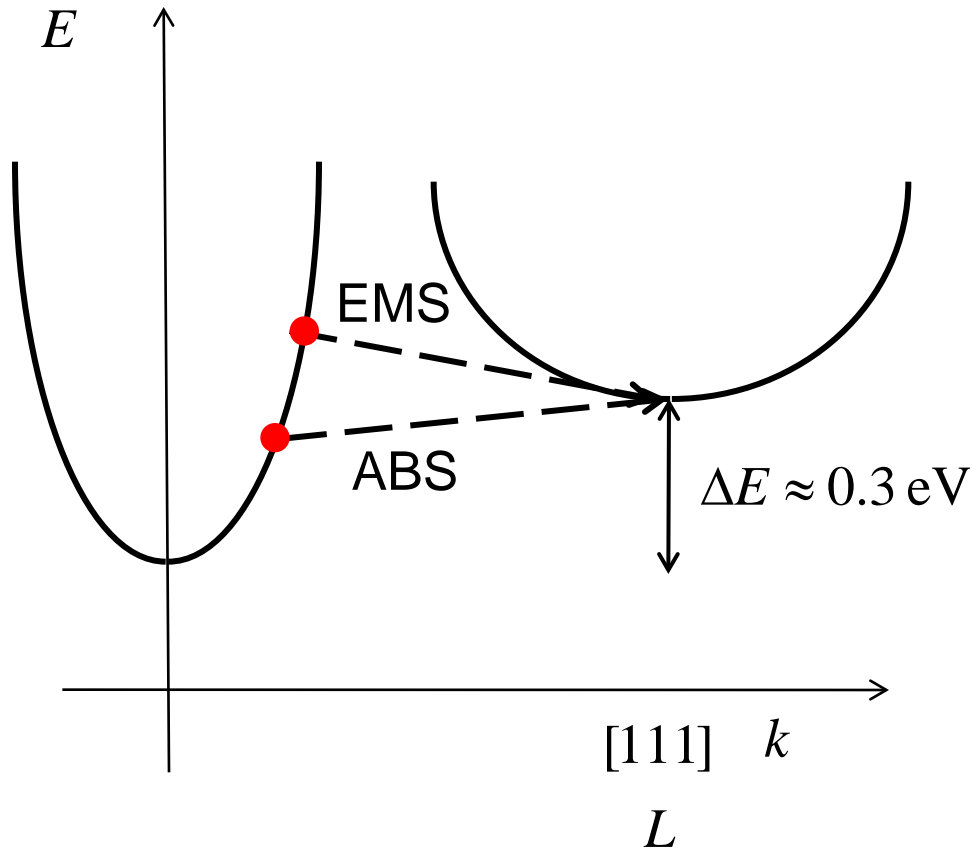
Lundstrom, FCT, pp. 84 – 86 for momentum and energy relaxation rates.



# POP scattering



# IV scattering (GaAs)



Requires phonons with momentum near the zone boundary.

# IV scattering (GaAs)

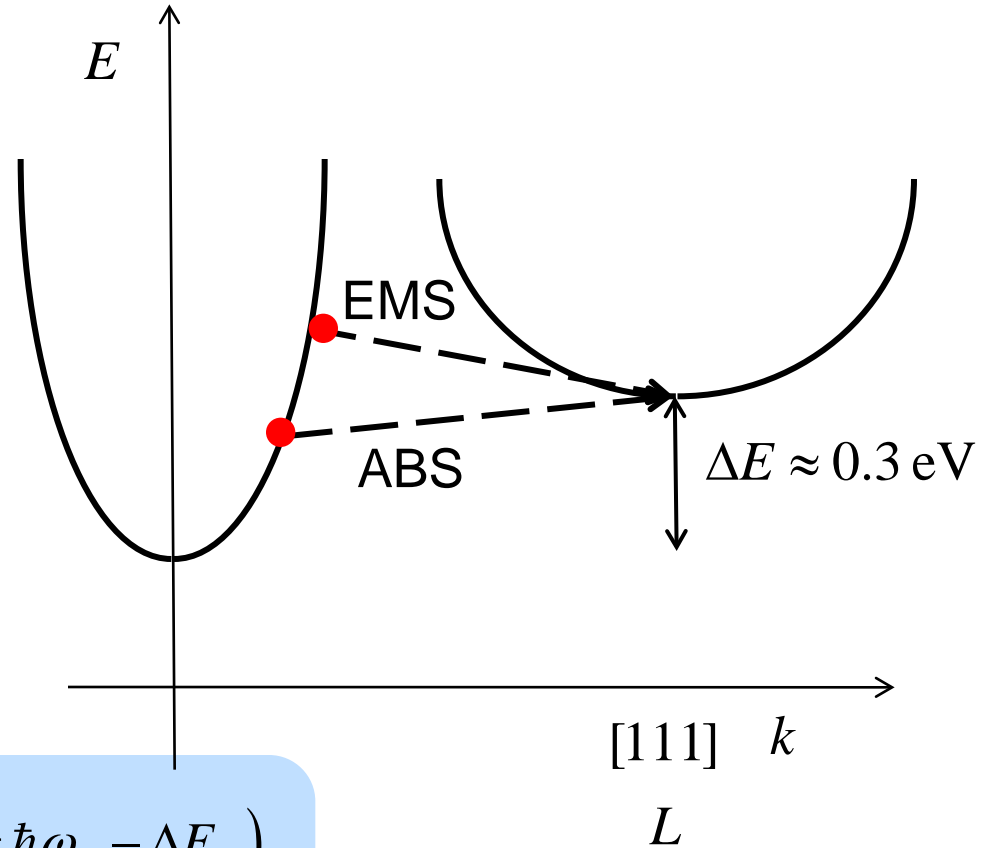
Postulate:

$$U_s = D_{if} u_\beta$$

Then IV scattering looks like  
ODP scattering

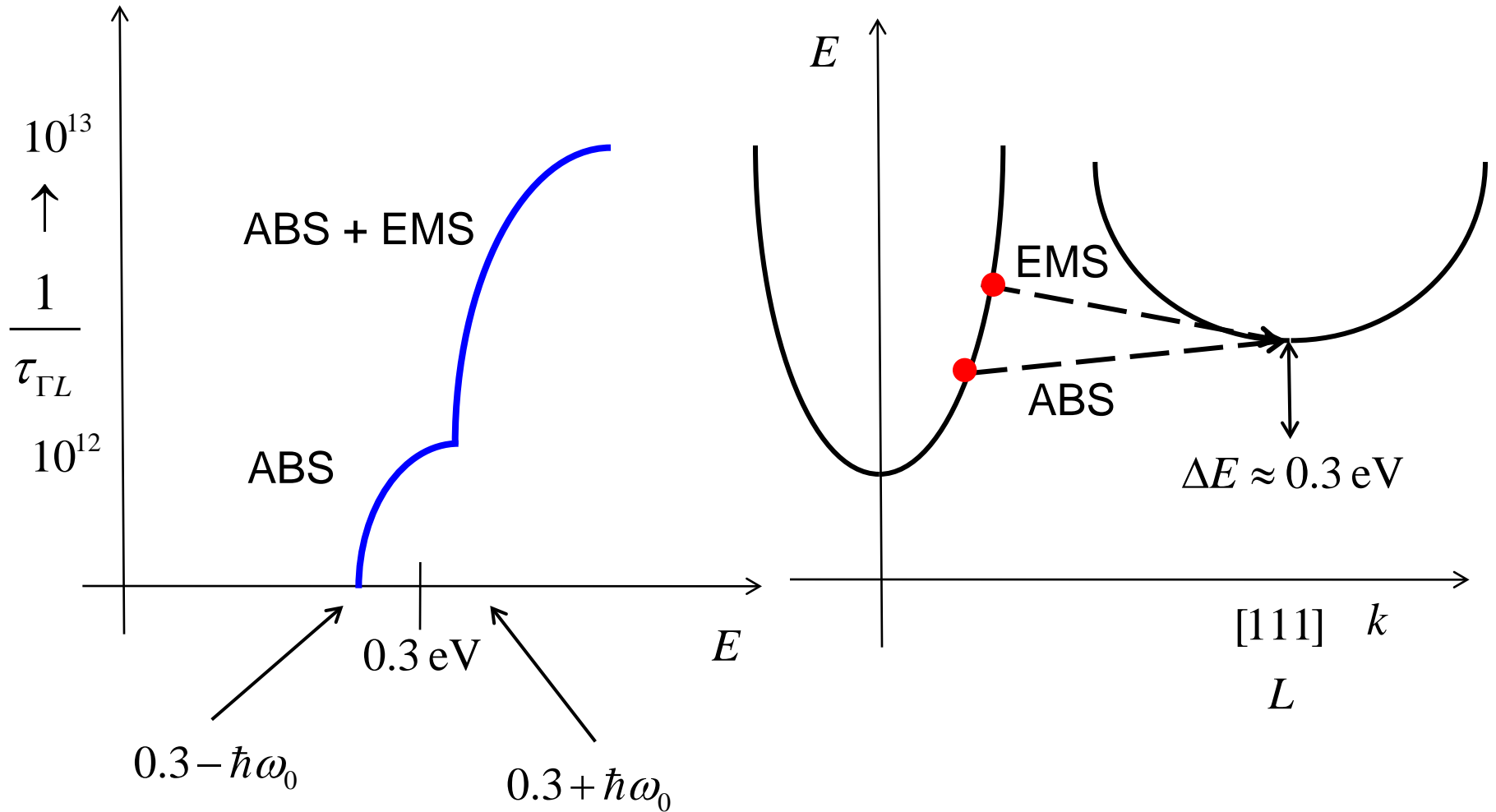
Isotropic:  $\frac{1}{\tau} = \frac{1}{\tau_m}$

Number of final valleys:  $Z_f$

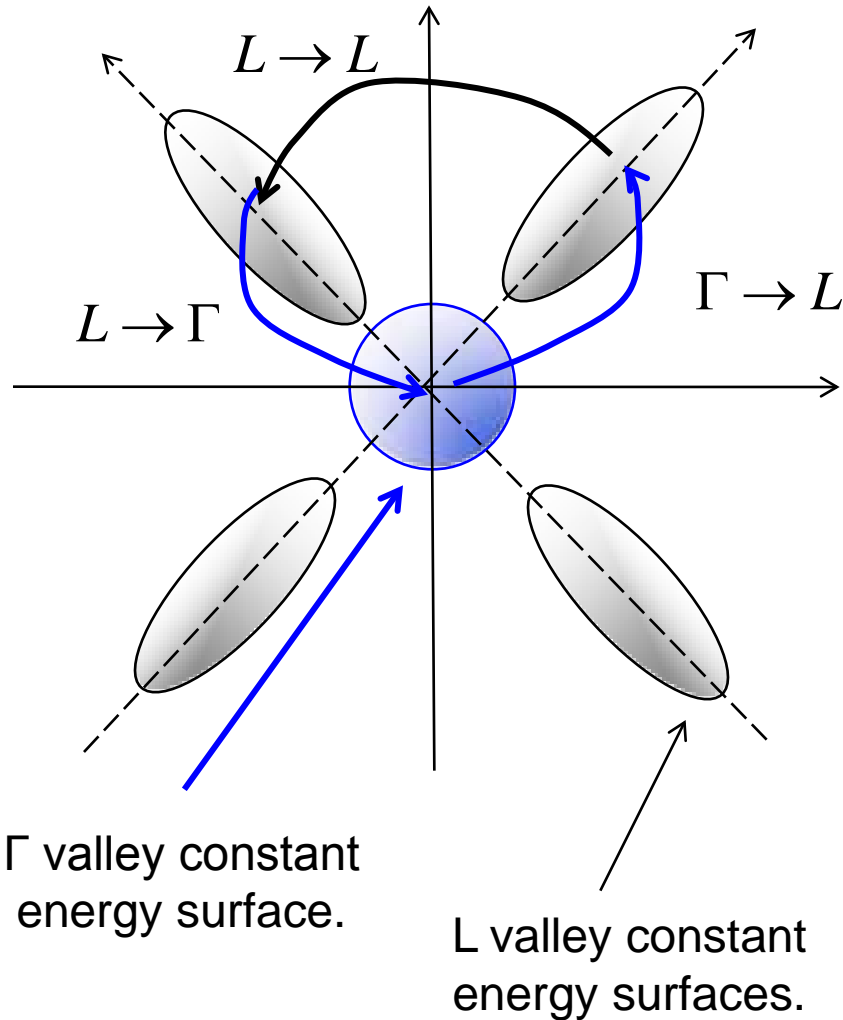


$$\frac{1}{\tau} = \frac{2\pi}{\hbar} \left( \frac{\hbar D_{if}^2 Z_f}{2\rho\omega_{if}} \right) \left( N_{if} + \frac{1}{2} \mp \frac{1}{2} \right) \frac{D_f (E \pm \hbar\omega_{if} - \Delta E_{fi})}{2}$$

# IV scattering (GaAs)



# L-L and L- $\Gamma$ IV scattering (GaAs)



$$\frac{1}{\tau} \propto D_{if}^2 Z_f \frac{D_f (E \pm \hbar\omega_{if} - \Delta E_{fi})}{2}$$

$$\Gamma \rightarrow L: Z_f = 4 \quad \Delta E_{fi} = 0.3 \text{ eV}$$

$$L \rightarrow L: Z_f = 3 \quad \Delta E_{fi} = 0 \text{ eV}$$

$$L \rightarrow \Gamma: Z_f = 1 \quad \Delta E_{fi} = -0.3 \text{ eV}$$

Compare rates:

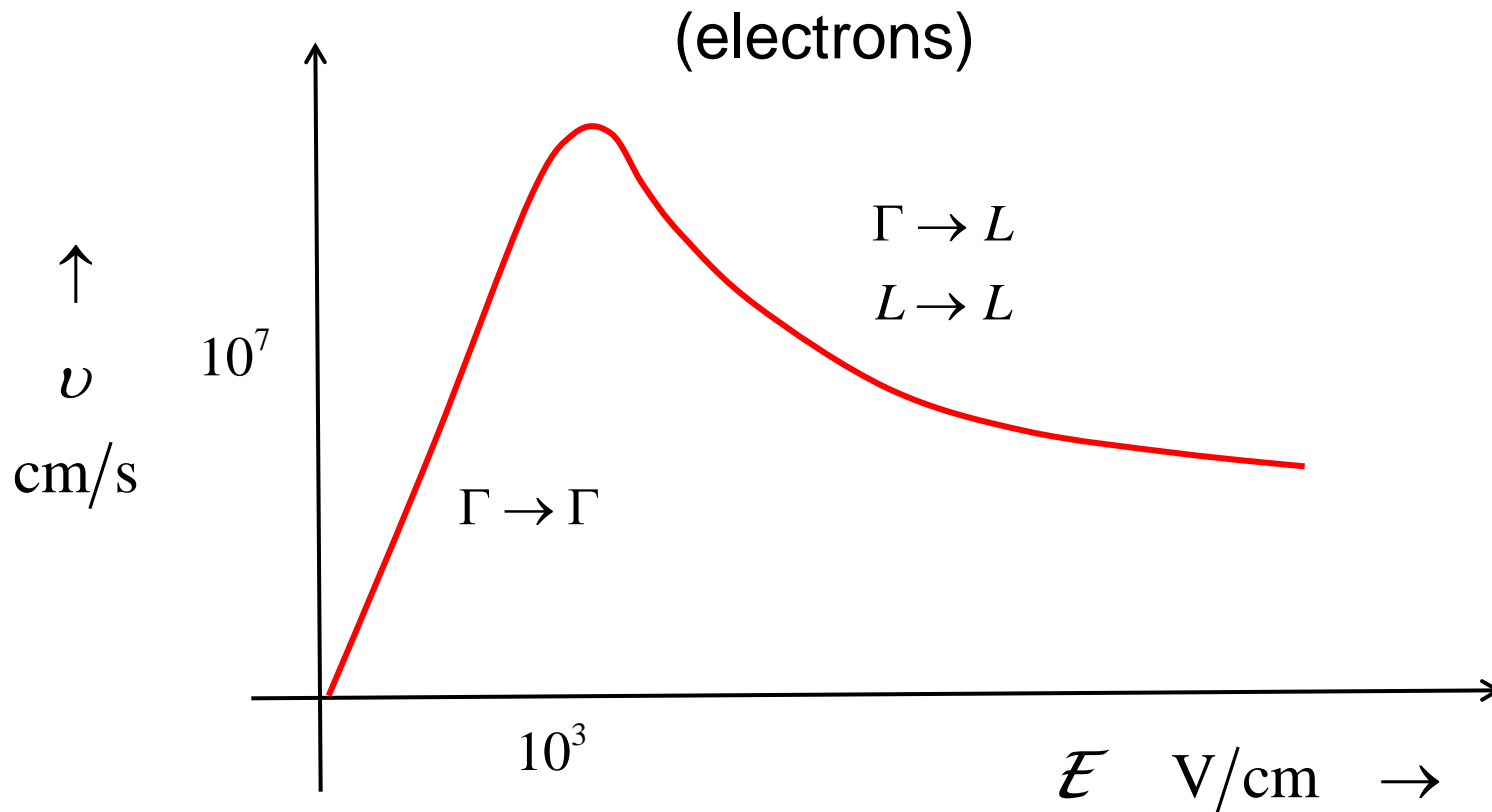
$$1/\tau_{\Gamma \rightarrow \Gamma} \quad (\text{POP})$$

$$1/\tau_{\Gamma \rightarrow L}$$

$$1/\tau_{L \rightarrow L}$$

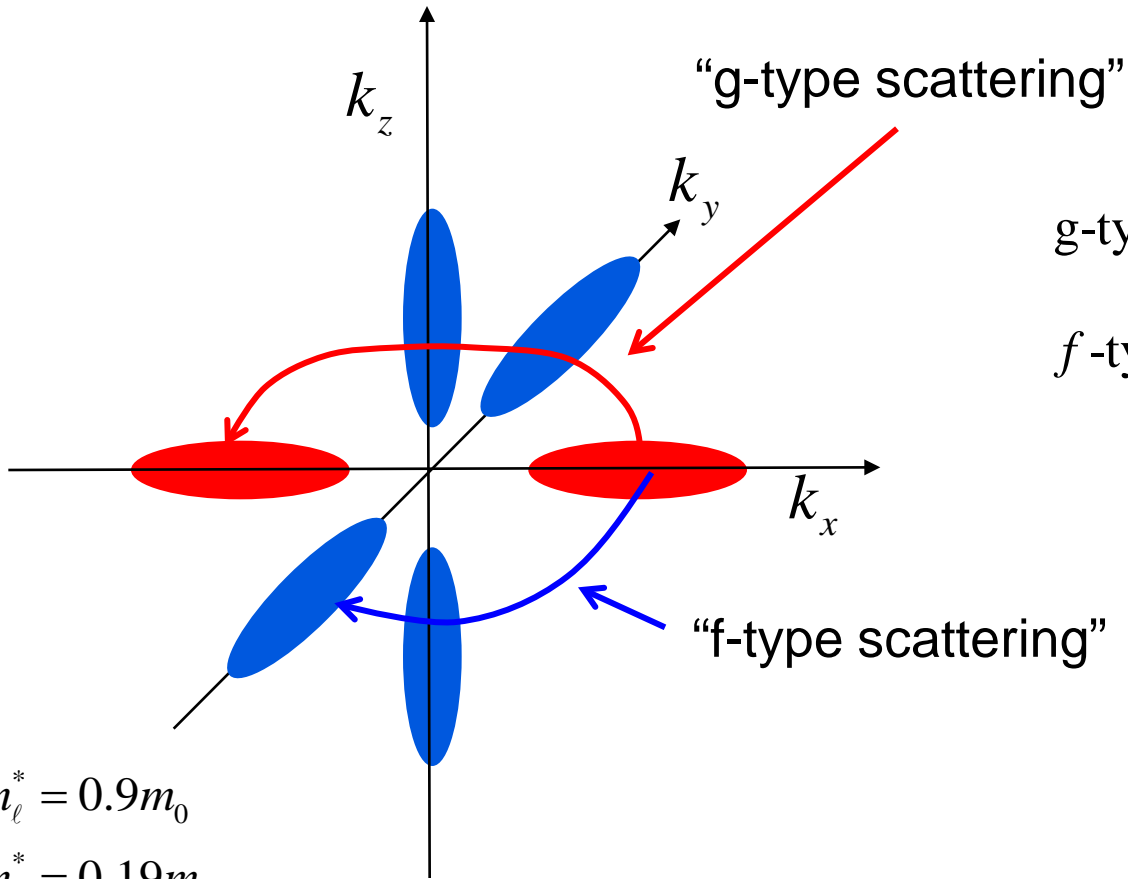
$$1/\tau_{L \rightarrow \Gamma}$$

# velocity vs. electric field: GaAs



# equivalent IV scattering (Si)

Si conduction band



$$m_\ell^* = 0.9m_0$$

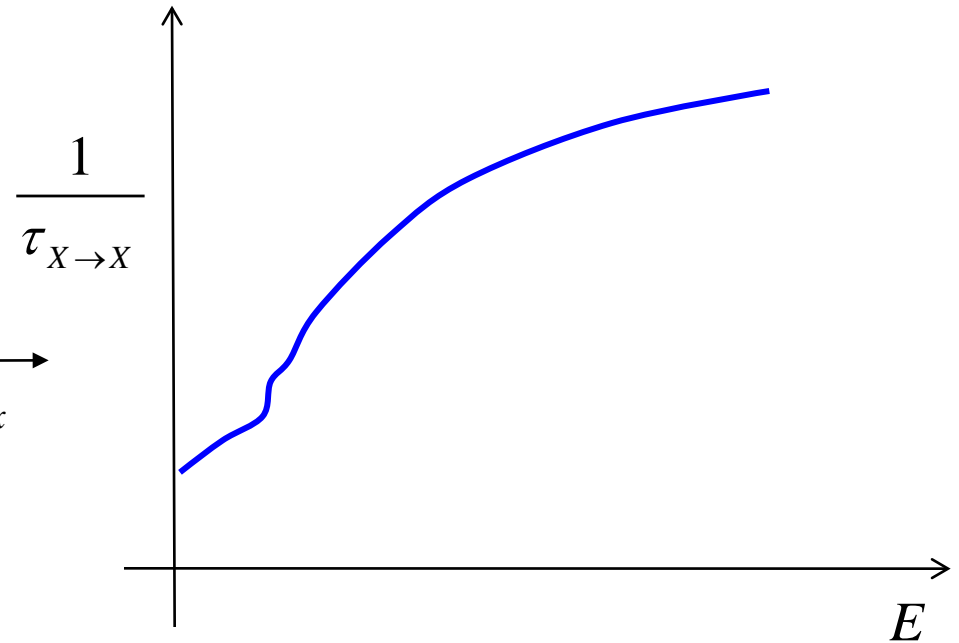
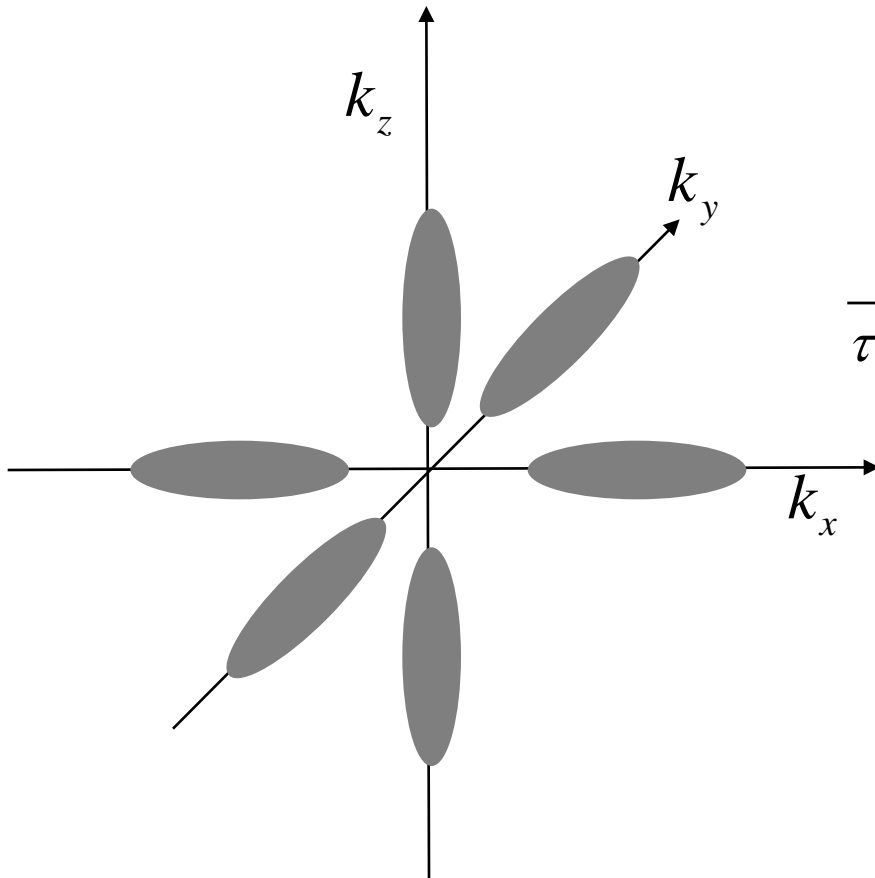
$$m_t^* = 0.19m_0$$

g-type:  $Z_f = 1 \quad \Delta E_{fi} = 0 \text{ eV}$

f-type:  $Z_f = 4 \quad \Delta E_{fi} = 0 \text{ eV}$

# equivalent IV scattering (Si)

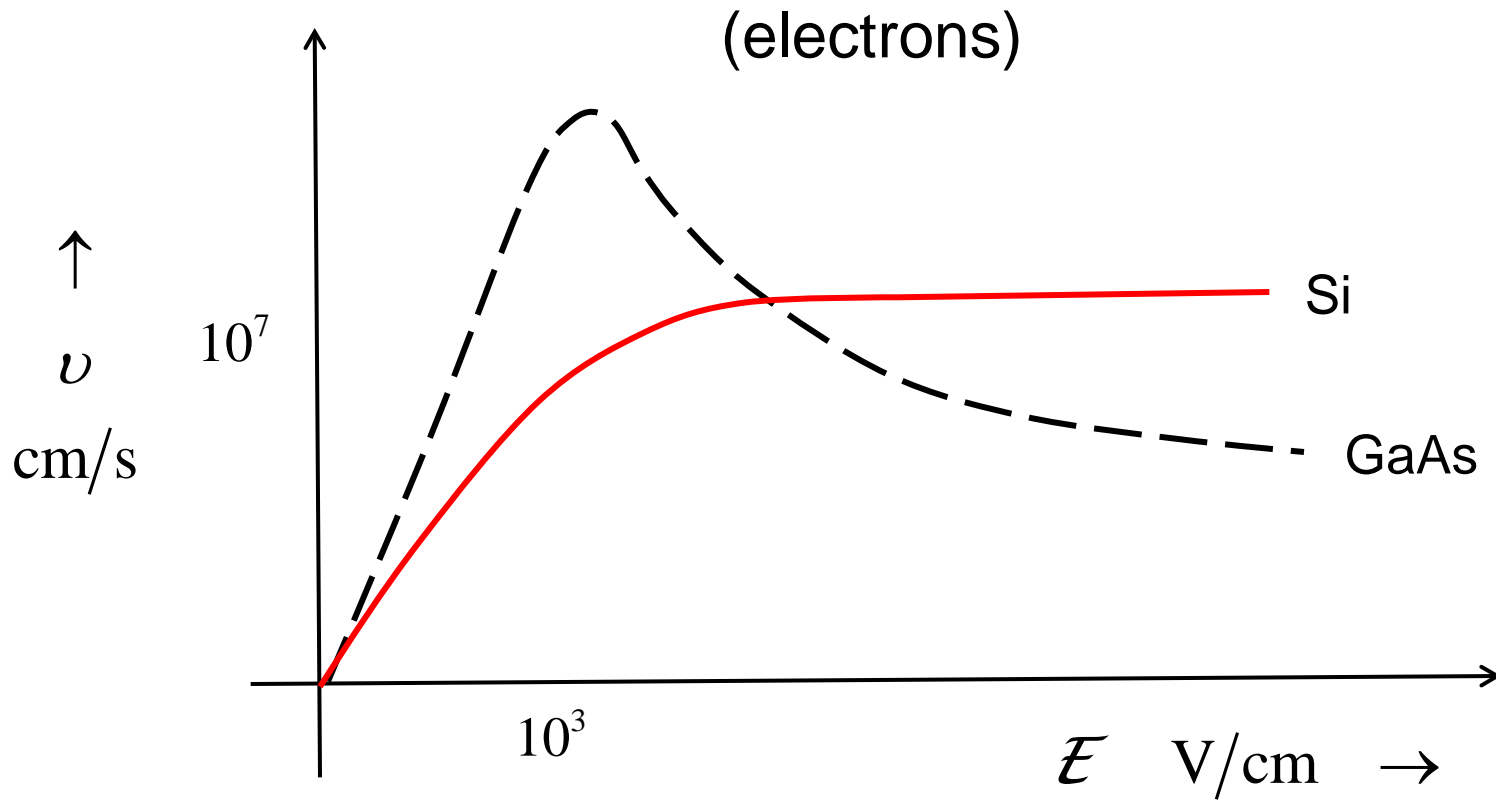
Si conduction band



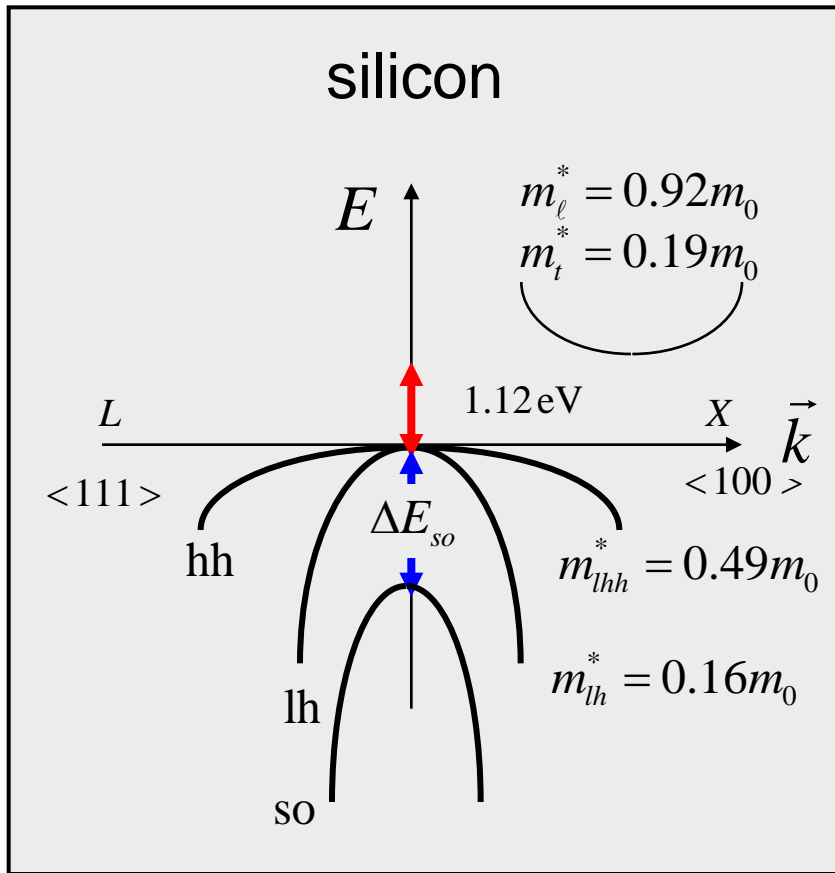
Important at room temperature in Si



# velocity vs. electric field: Si



# about holes



$$\Delta E_{so} = 44 \text{ meV (Si)}$$

$$= 290 \text{ meV (Ge)}$$

Intravalley:

$$\frac{1}{\tau_{hh \rightarrow hh}} \quad \frac{1}{\tau_{lh \rightarrow lh}} \quad \frac{1}{\tau_{so \rightarrow so}}$$

Intervalley:

$$\frac{1}{\tau_{hh \rightarrow lh}} \quad \frac{1}{\tau_{lh \rightarrow hh}}$$

$$\frac{1}{\tau_{hh \rightarrow so}} \quad \frac{1}{\tau_{so \rightarrow hh}} \quad \frac{1}{\tau_{lh \rightarrow so}} \quad \frac{1}{\tau_{so \rightarrow lh}}$$

Valence band is complex (warped) and can be engineered by strain.

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# key questions

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1) What is the total scattering rate vs. energy for common semiconductors?

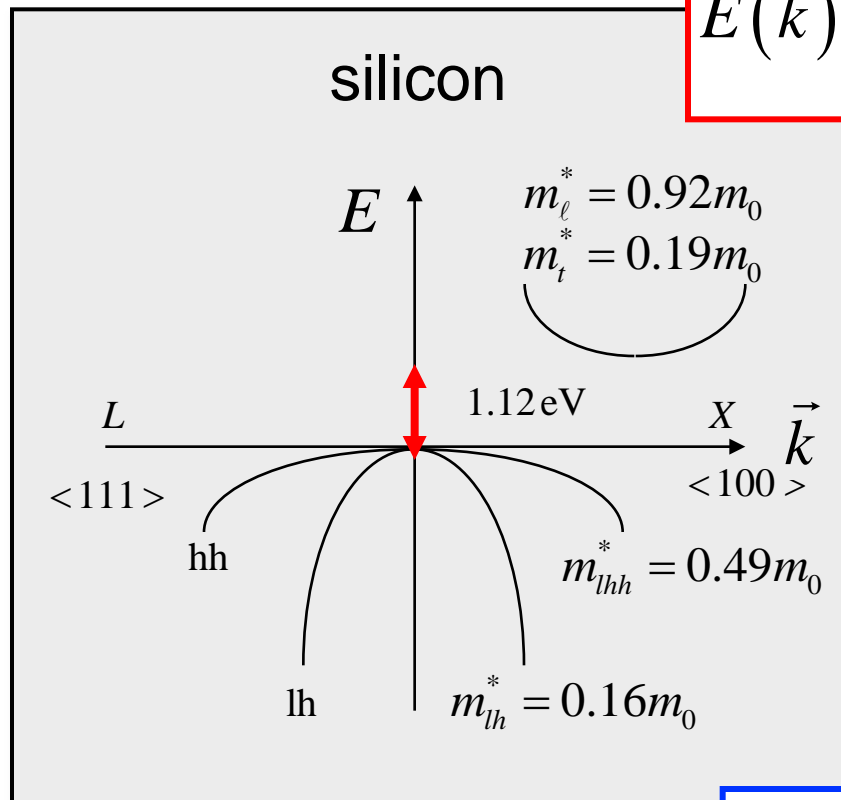
$$\Gamma = \sum_i \frac{1}{\tau_i}$$

2) How do covalent semiconductors (e.g. Si, Ge) differ from polar semiconductors (e.g. GaAs, InP, InGaAs, ZnSe)?

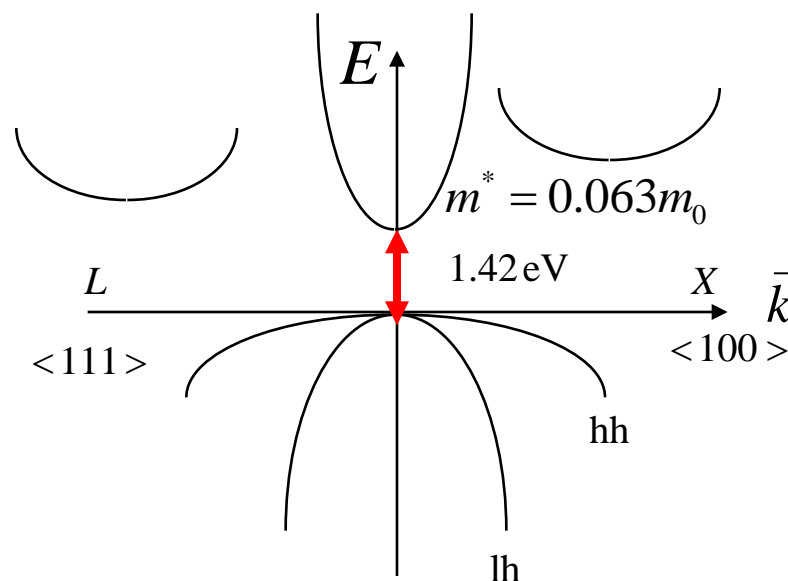
# model bandstructure (for analytical calculations)

Si, covalent, indirect BG

$$E(k) = E_C + \frac{\hbar^2 k^2}{2m_n^*}$$

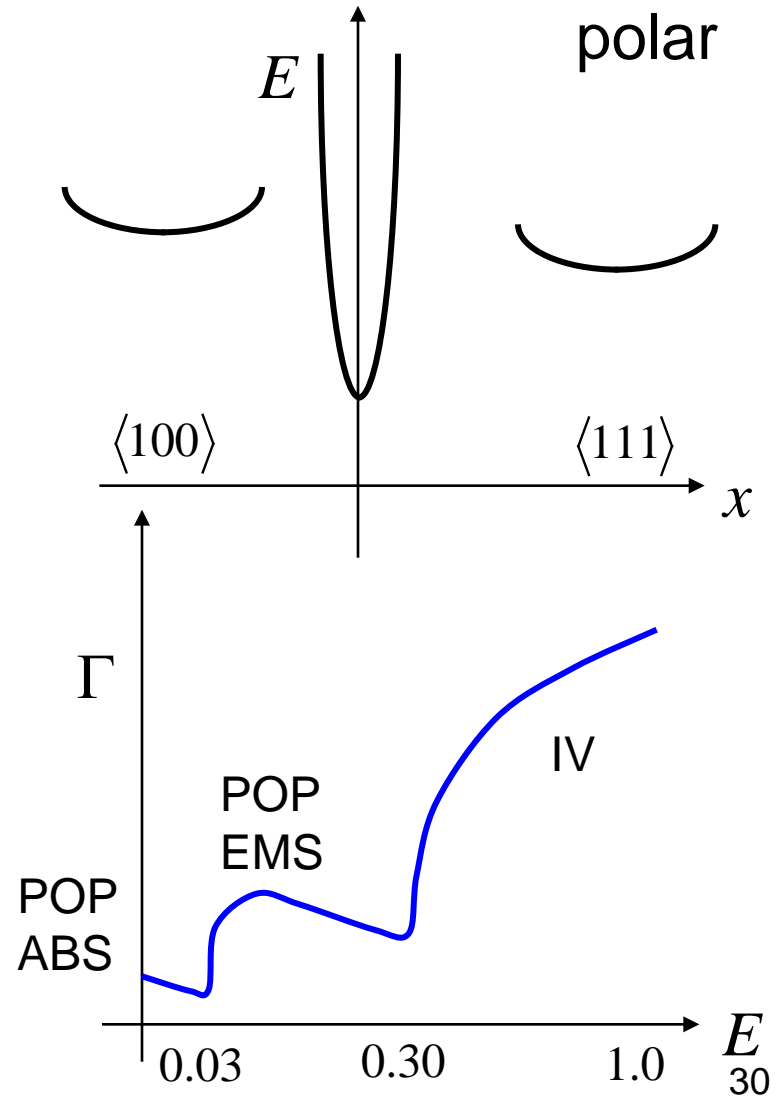
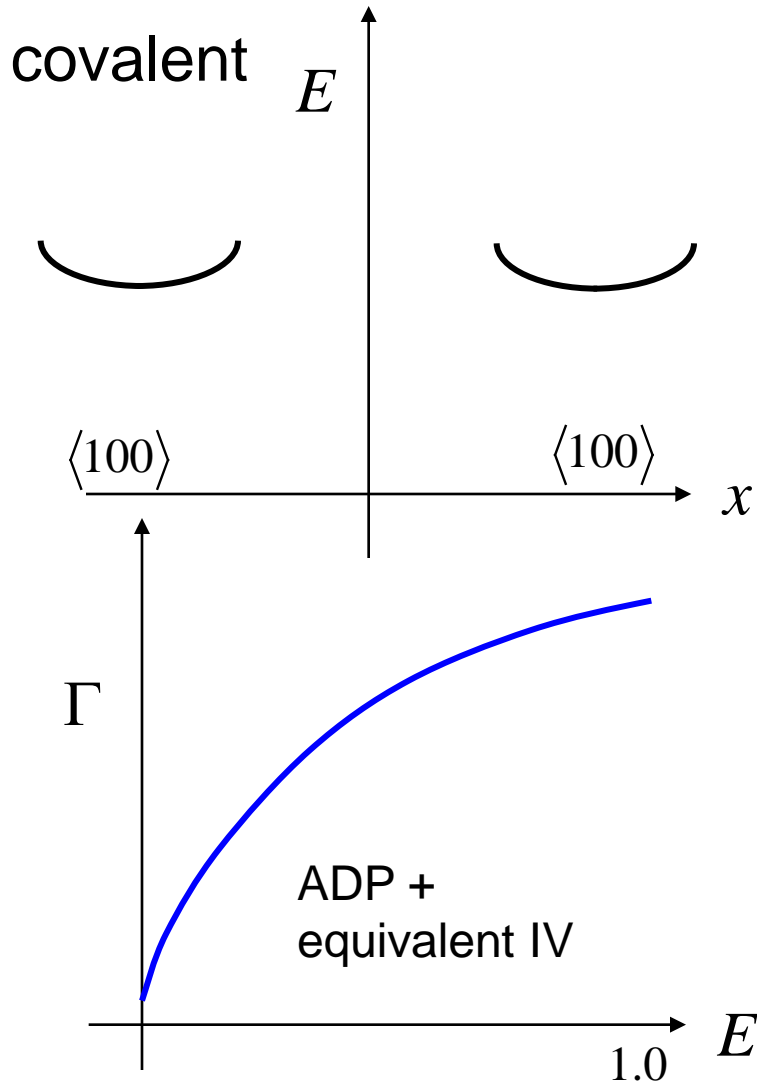


GaAs



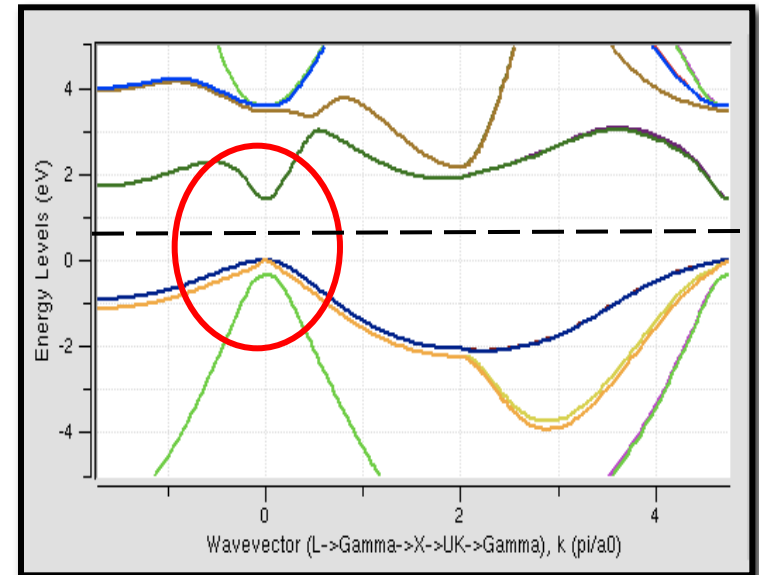
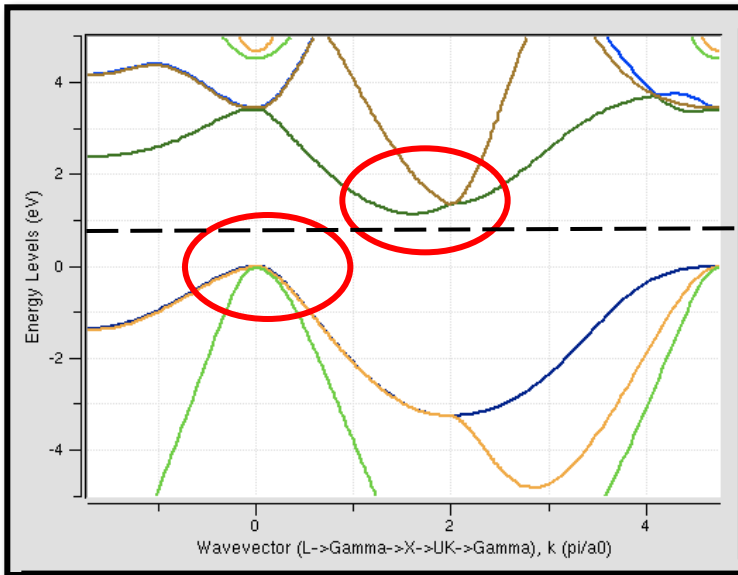
$$E(k) = E_V - \frac{\hbar^2 k^2}{2m_p^*}$$

# covalent vs. polar semiconductors



# energy bands

Si, covalent, indirect bandgap



# “full band” scattering rates

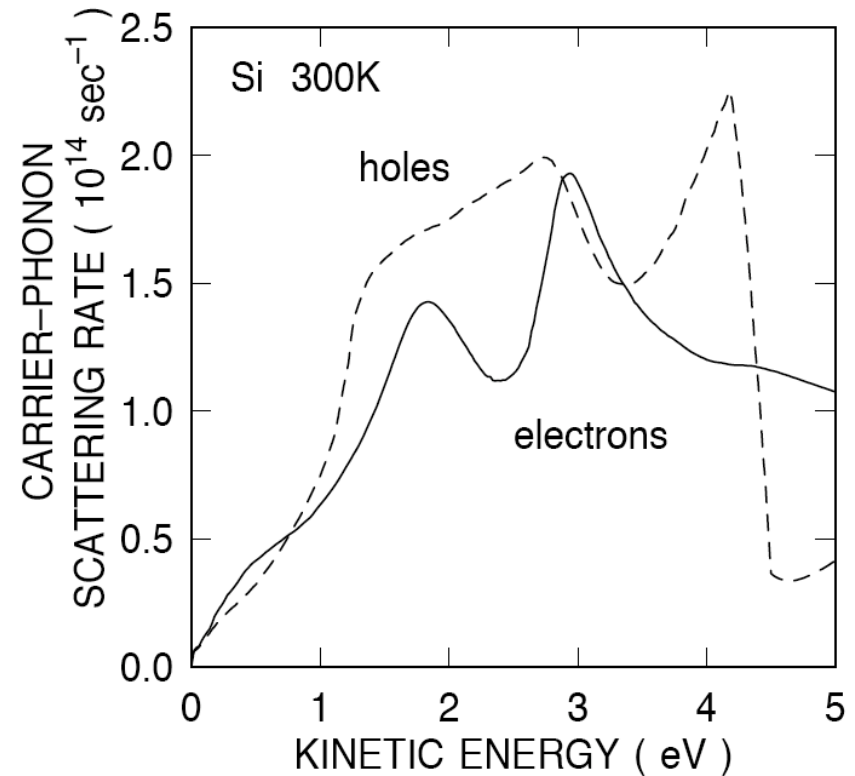
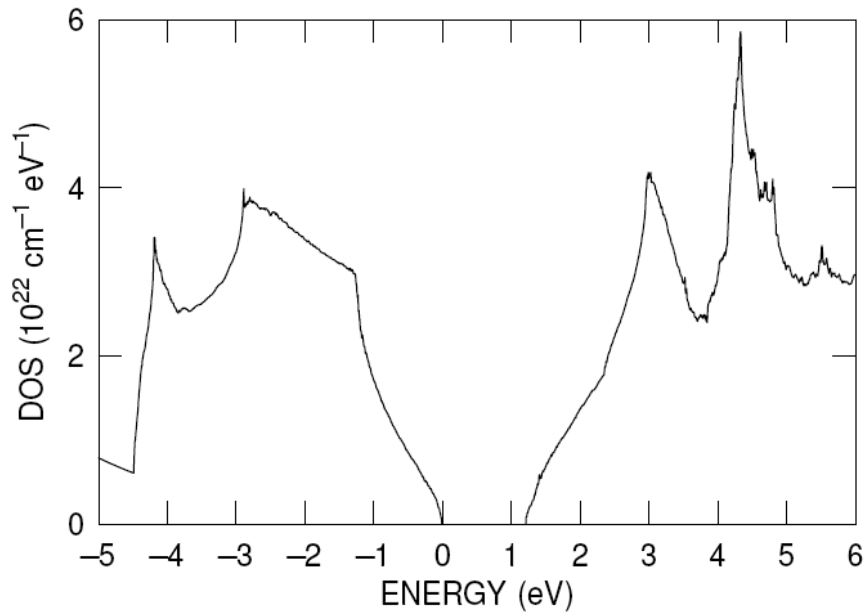
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For a good, general reference on the numerical evaluation of scattering rates in common semiconductors, see:

- [1] Massimo V. Fischetti, Monte Carlo Simulation of Transport in Technologically Significant Semiconductors of the Diamond and Zinc-Blende Structures-Part I: Homogeneous Transport,” *IEEE Trans. Electron Dev.*, **38**, pp. 634-649, 1991
  
- [2] M. V. Fischetti, N. Sano, S. E. Laux, and K. Natori, “Full-bandstructure theory of high-field transport and impact ionization of electrons and holes in Ge, Si, GaAs, InAs, and  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ ,” *unpublished manuscript.*, January 3, 2001.

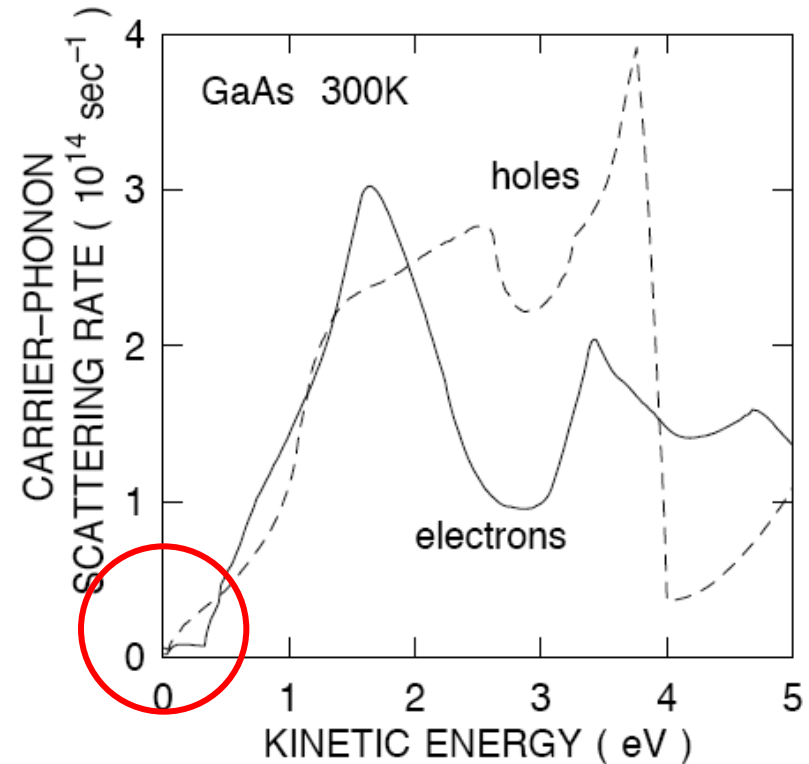
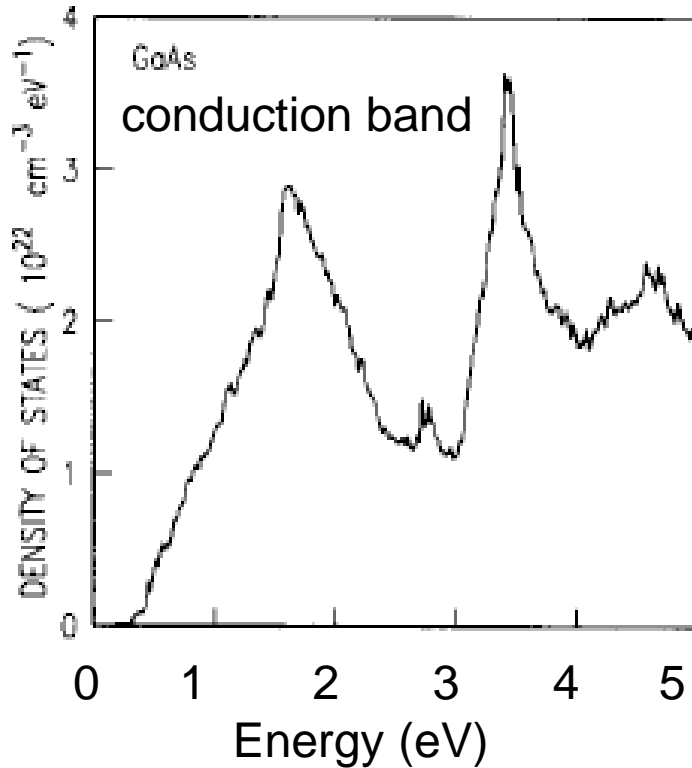


# electrons and holes in Si



[2] Figures provided by Massimo V. Fischetti, October, 2009.

# electrons and holes in GaAs



DOS: [1] M. V. Fischetti, " *IEEE Trans. Electron Dev.*, **38**, pp. 634-649, 1991  
Scattering rate: [2] Provided by M. V. Fischetti, October, 2009)

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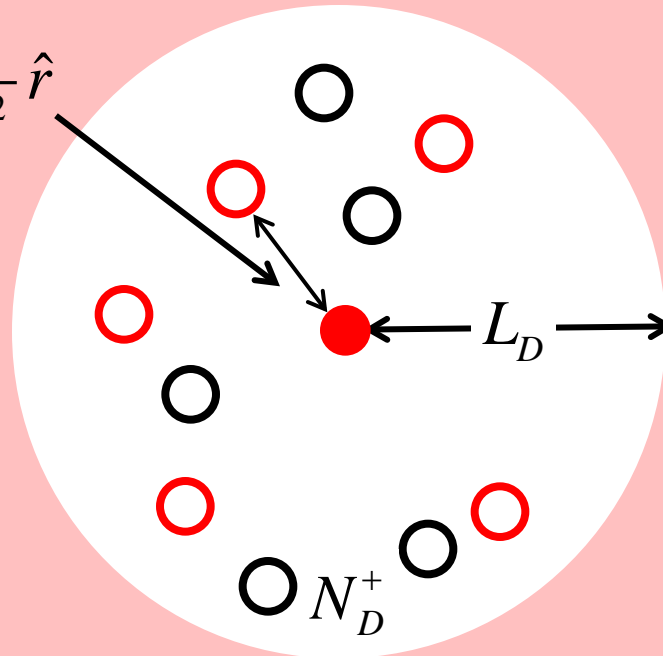
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# long and short range Coulomb effects

$$\vec{F}_e(\vec{r}, t) = -q\vec{E}(\vec{r}, t)$$

$$\nabla \cdot [\kappa_s \epsilon_0 \vec{E}(\vec{r}, t)] = \rho(\vec{r}, t)$$

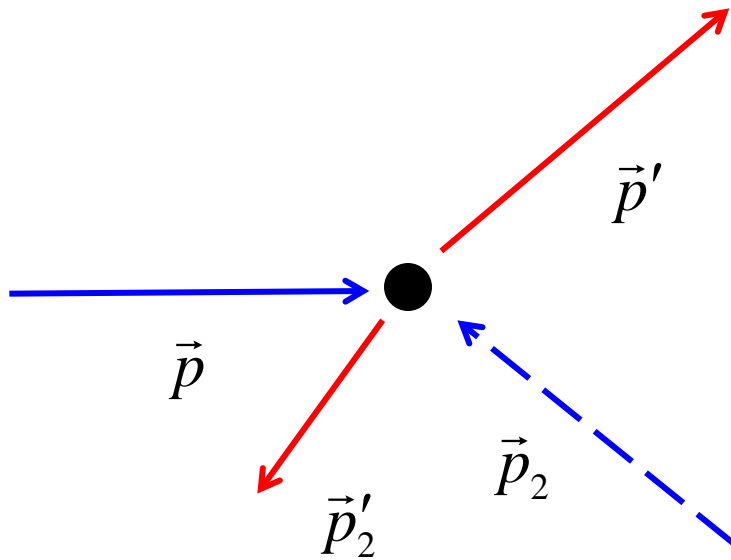
$$\vec{F}_e(\vec{r}, t) = \frac{q_1 q_2}{4\pi \kappa_s \epsilon_0 r^2} \hat{r}$$



$$n_0 \text{ cm}^{-3}$$

$$\rho = q(N_D^+ - n_0) \text{ C/cm}^{-3}$$

# binary e-e scattering



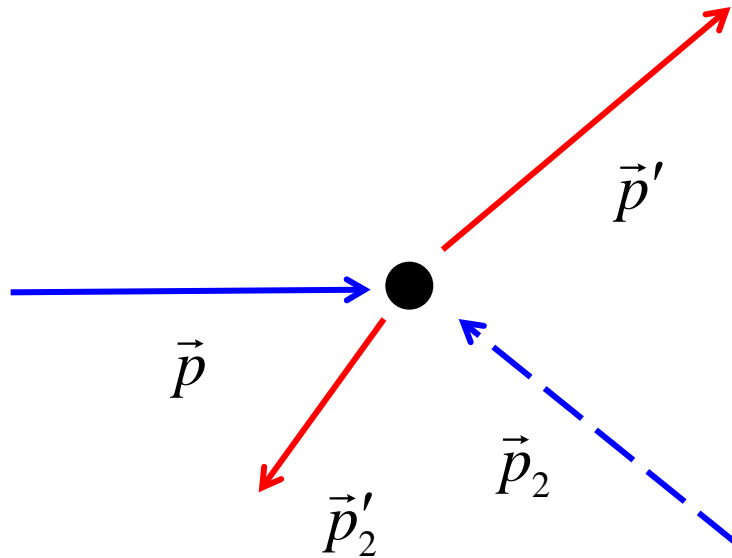
$$\vec{p} + \vec{p}_2 = \vec{p}' + \vec{p}'_2$$

$$E + E_2 = E' + E'_2$$

Important when  $n > \sim 10^{17} \text{ cm}^{-3}$

$$S(\vec{p}, \vec{p}') \rightarrow S(\vec{p}, \vec{p}_2; \vec{p}', \vec{p}'_2)$$

# binary e-e scattering rate



$$\frac{1}{\tau} = \sum_{\vec{p}'} S(\vec{p}, \vec{p}') \rightarrow$$

Important when  $n > \sim 10^{17} \text{ cm}^{-3}$

$$\frac{1}{\tau_{e-e}} = \sum_{\vec{p}', \vec{p}_2} S(\vec{p}, \vec{p}_2; \vec{p}', \vec{p}'_2) f(\vec{p}_2) [1 - f(\vec{p})] [1 - f(\vec{p}'_2)]$$

(a very difficult problem to solve)

# e-e scattering

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When e-e- scattering dominates, electrons exchange energy among themselves and an equilibrium shape (Maxwellian or Fermi-Dirac) distribution is established.

$$f(\vec{p}) \propto e^{-p^2/2mk_B T_e}$$

The electron temperature, however, may be quite different from the lattice temperature.

To first order, electron-electron scattering does not lower the mobility, because the total momentum of the electron system is conserved, but there can be an indirect effect because the shape of the distribution affects the average scattering rate for other scattering processes.

# outline

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- 1) Review
- 2) Example
- 3) POP and IV scattering
- 4) Scattering in common semiconductors
- 5) Electron-electron scattering
- 6) Summary**

(Reference: Chapter 2, Lundstrom, FCT)



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